



arm

Shaping the future of the connected world with FinFET and FDSOI

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13th May 2019

The connected world of today



Create & Distribute

Media Content



Billions
of Phones



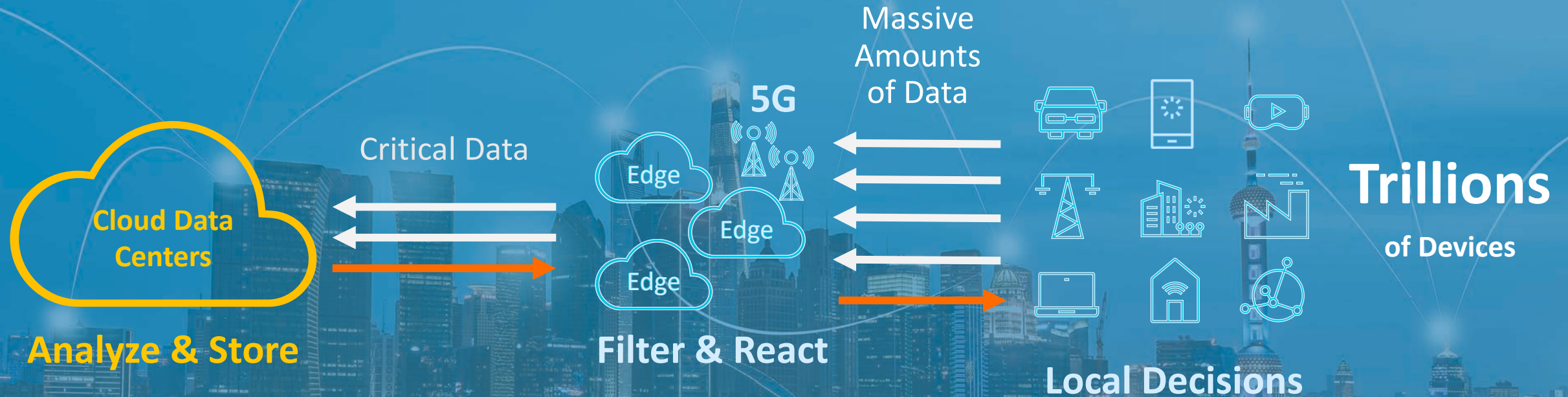
Consume

Fifth wave: next wave of computing

AI

5G

Looking ahead to a new connected world



But different markets have different needs

Mobile and Consumer

- High performance
- Low power
- Cost (area) sensitive
- Flexible performance requirements



Mainstream

- 16/14/12/11nm
- 10/8nm

Premium

- 7/5nm

Networking and Servers

- High performance
- Fault tolerance
- Long lifetime
- Continuous operation



Networking

- 7/5nm
- 16/14/11nm
- 10/8nm

Server

- 7/5nm

Automotive

- High temperature
- Fault tolerance
- Long lifetime
- Low power
- Non-volatile memory



Engine & Body Control

- 55/40nm
- >130nm

ADAS, self driving

- 7nm
- 16/14nm
- FDSOI
- eMRAM

IoT

- Very low power
- Low voltage
- Very low cost
- Non-volatile memory



Ultra Low Power

- >40nm
- 28/22nm
- eMRAM
- FDSOI

Advanced Applications

- 16/14/12/11nm

Foundry market snapshot

Foundry Market by Feature Dimension

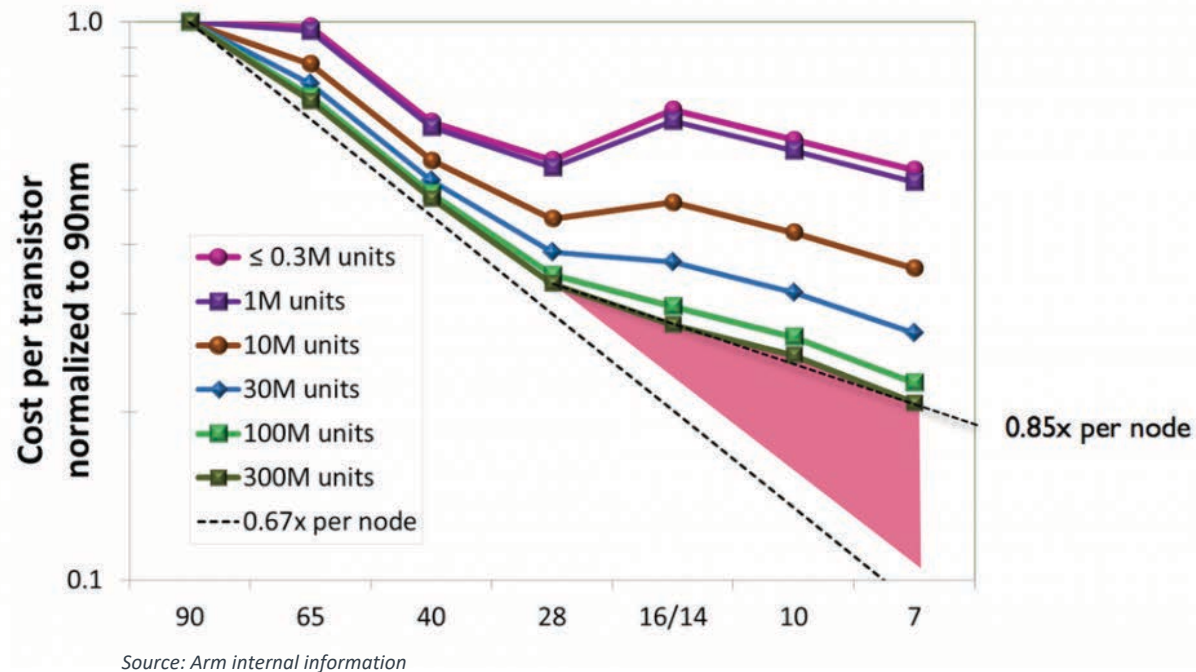
	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
≤5nm (\$M)	--	--	--	374	3,785	6,495	8,794	10,961	13,264	15,896	18,958
Growth rate (%)	--	--	--	NA	912.03	71.60	35.40	24.64	21.01	19.84	19.26
7nm (\$M)	--	3,071	11,194	12,931	13,253	13,337	13,412	13,475	13,486	13,456	13,423
Growth rate (%)	--	NA	264.51	15.52	2.49	0.63	0.56	0.47	0.08	(0.22)	(0.25)
10nm (\$M)	4,692	4,770	2,581	2,490	2,362	2,152	1,927	1,637	1,340	1,151	989
Growth rate (%)	NA	1.66	(45.89)	(3.53)	(5.14)	(8.89)	(10.46)	(15.05)	(18.14)	(14.10)	(14.07)
16/14/12nm (\$M)	10,857	11,453	10,138	9,091	8,611	7,914	7,540	7,270	6,948	6,651	6,447
Growth rate (%)	NA	5.49	(11.48)	(10.33)	(5.28)	(8.09)	(4.73)	(3.58)	(4.43)	(4.27)	(3.07)
28/22/20/18nm (\$M)	11,802	9,782	8,862	8,617	9,022	9,759	10,623	11,596	12,735	13,956	15,216
Growth rate (%)	NA	(17.12)	(9.41)	(2.76)	4.70	8.17	8.85	9.16	9.82	9.59	9.03
45/40nm (\$M)	7,825	7,287	6,725	6,545	6,741	6,816	6,737	6,668	6,584	6,496	6,401
Growth rate (%)	NA	(6.88)	(7.71)	(2.68)	2.99	1.11	(1.16)	(1.02)	(1.26)	(1.34)	(1.46)
65nm (\$M)	7,153	6,742	6,416	6,326	6,515	6,529	6,518	6,503	6,484	6,462	6,432
Growth rate (%)	NA	(5.75)	(4.84)	(1.40)	2.99	0.21	(0.17)	(0.23)	(0.29)	(0.34)	(0.46)
90nm (\$M)	1,982	1,836	1,863	1,795	1,771	1,733	1,681	1,628	1,573	1,516	1,459
Growth rate (%)	NA	(7.37)	1.47	(3.65)	(1.34)	(2.15)	(3.00)	(3.15)	(3.38)	(3.62)	(3.76)
0.13μm (\$M)	4,502	4,591	4,225	4,038	4,142	4,295	4,418	4,530	4,642	4,740	4,830
Growth rate (%)	NA	1.98	(7.97)	(4.43)	2.58	3.69	2.86	2.54	2.47	2.11	1.90
0.18/0.15μm (\$M)	6,034	6,325	6,390	6,582	6,762	6,901	7,207	7,598	8,024	8,477	8,907
Growth rate (%)	NA	4.82	1.03	3.00	2.73	2.06	4.43	5.43	5.61	5.65	5.07
≥0.25μm (\$M)	5,022	5,298	5,563	5,784	6,017	6,315	6,676	7,093	7,601	8,181	8,813
Growth rate (%)	NA	5.50	5.00	3.97	4.03	4.95	5.72	6.25	7.16	7.63	7.73
TOTAL (\$M)	59,869	61,155	63,957	64,573	68,981	72,246	75,533	78,959	82,681	86,982	91,875
Growth rate (%)	NA	2.15	4.58	0.96	6.83	4.73	4.55	4.54	4.71	5.20	5.63

Summary

- 5nm & below expected to have double digit % growth largely driven by mobile and server requirements
- 7nm shows negligible growth
- 28/22/18nm shows strong growth

But advanced designs are not for everyone

Gate cost trends

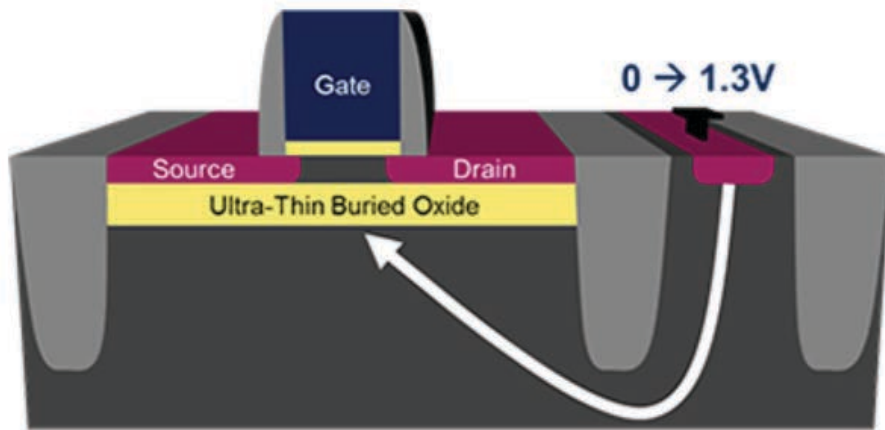


- There is still a cost benefit to move to advanced nodes if your volume is high for digital logic dominated SoC's
- Around 10M units, the benefit of moving to advanced nodes diminishes, even for digital logic
- Analog IP does not shrink in the same way, so staying around 28nm becomes a good node

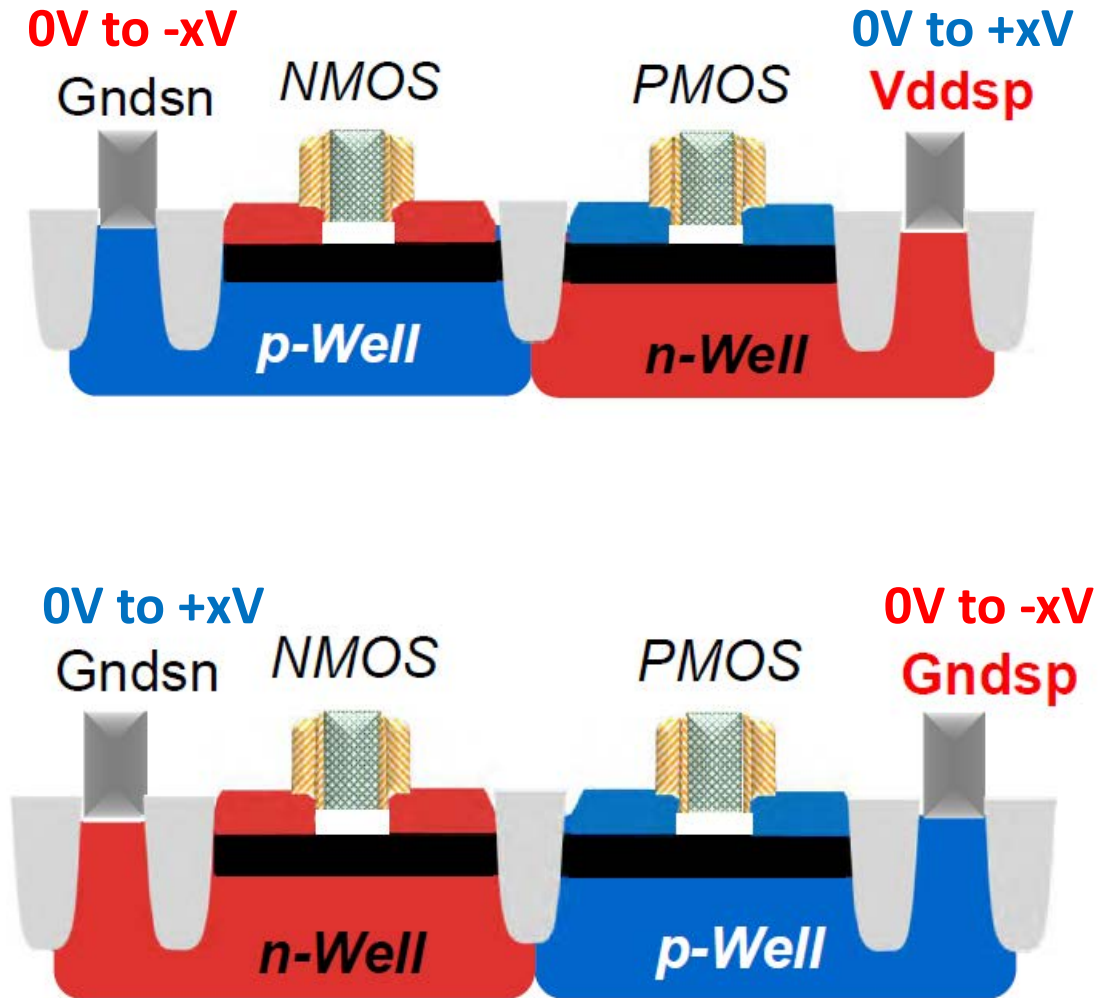
Step into the world of FDSOI

Key differentiator with respect to FinFET & Bulk

Speed/Power optimization

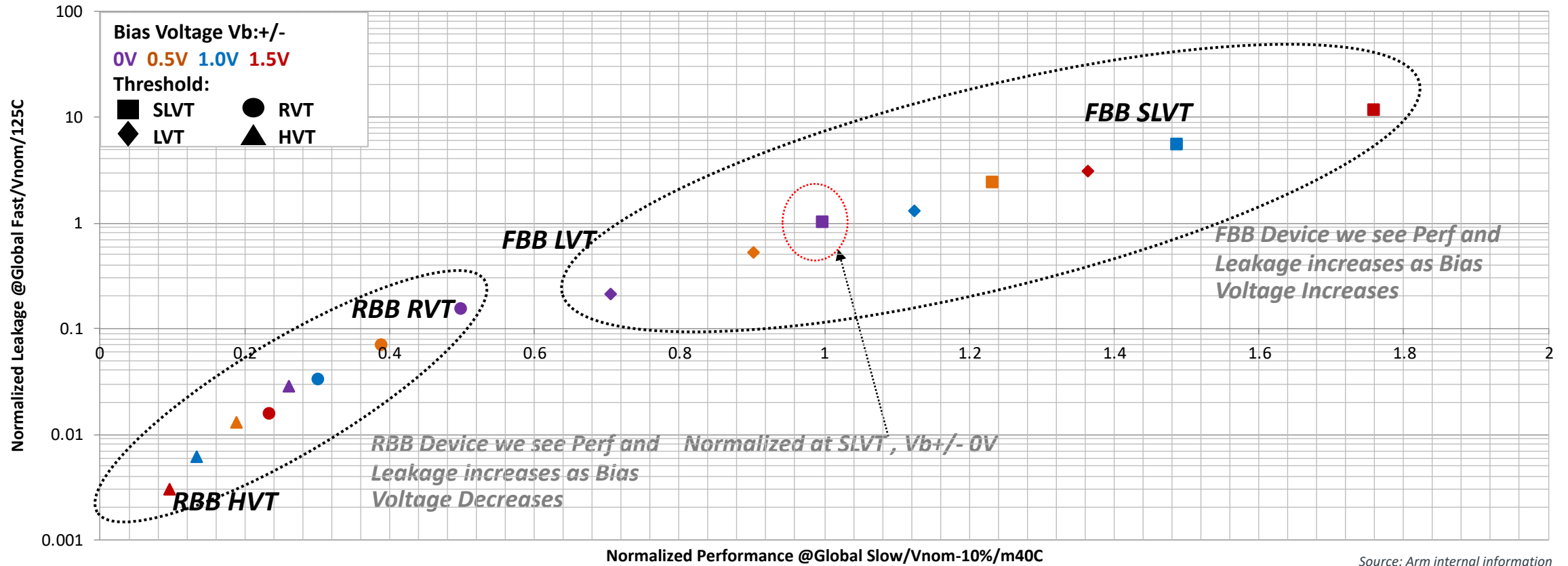


- Modulate transistor V_t for speed / power control
- No area penalty compared to bulk



Wide-range of design optimization points

Leakage vs. Performance

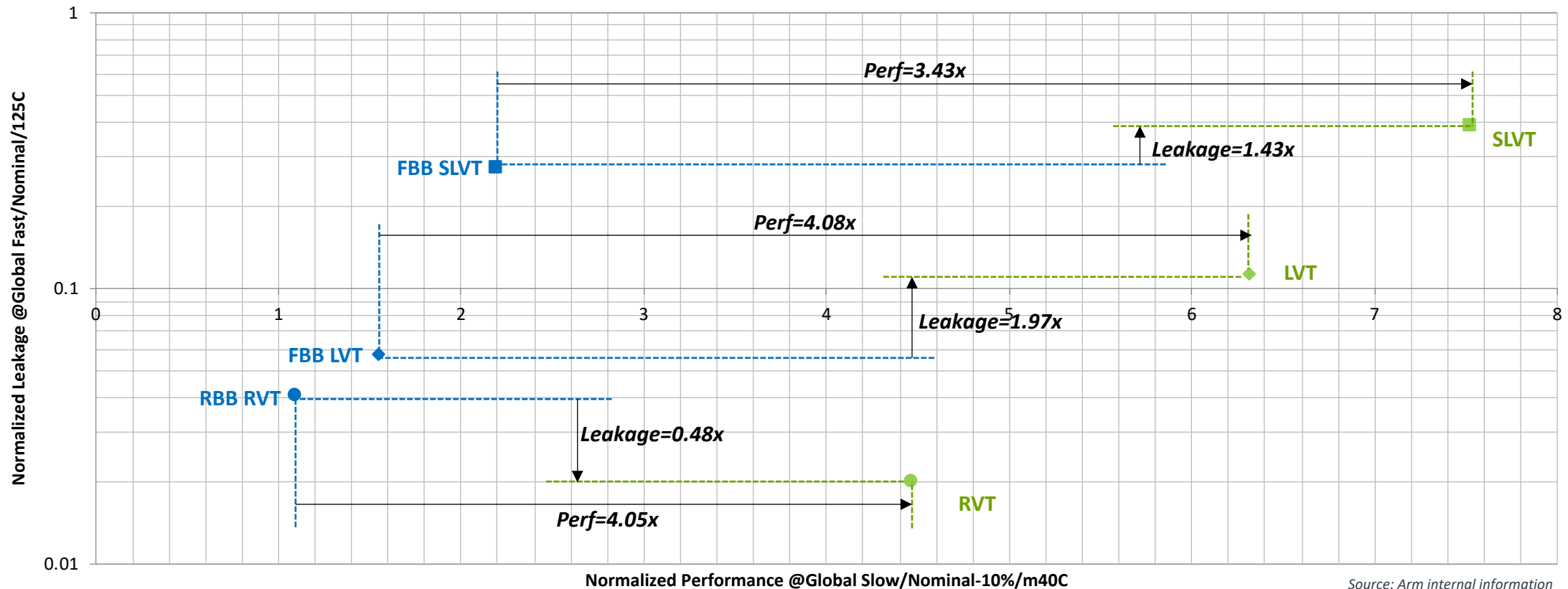


Source: Arm internal information

A comparison between FDSOI and FinFET @Global Corner

Bias Voltage = 0V

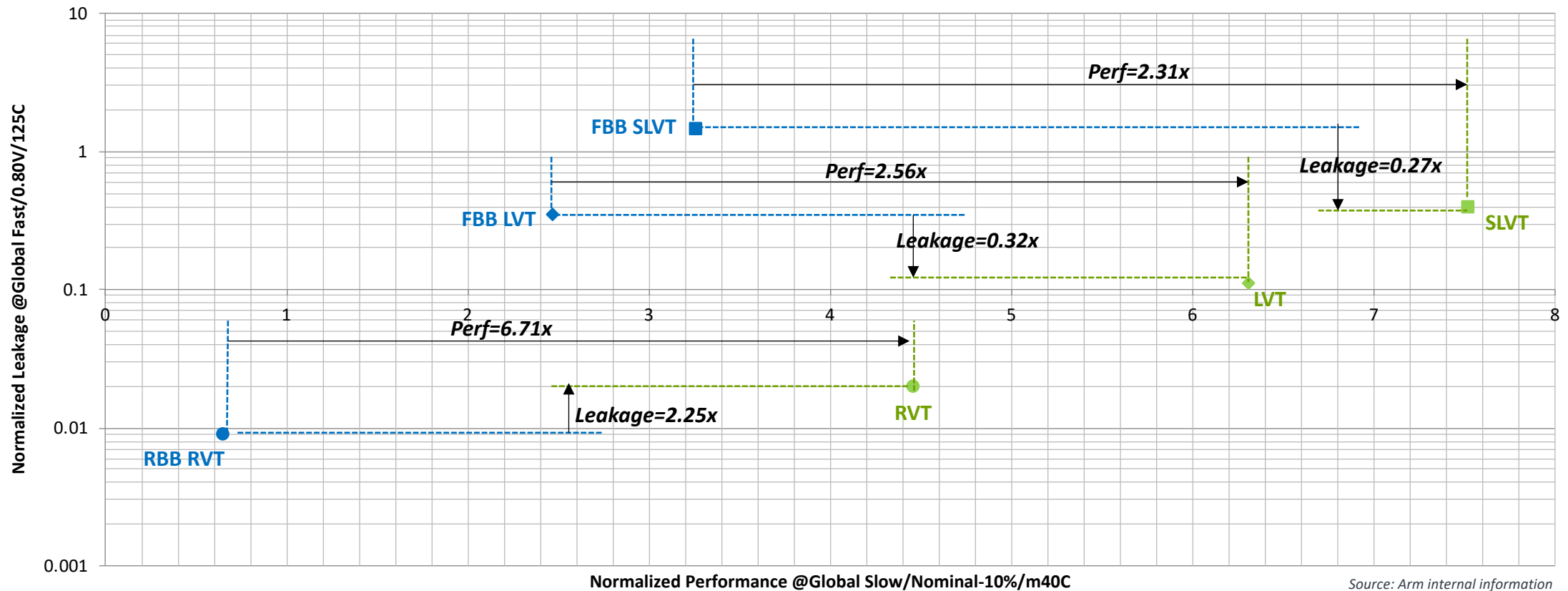
Leakage vs. Performance



A comparison between FDSOI and FinFET @Global Corner

Bias Voltage = 1V,-1V

Leakage vs. Performance



DVFS vs Body Bias

Need lot of PVT corners to take advantage of body bias

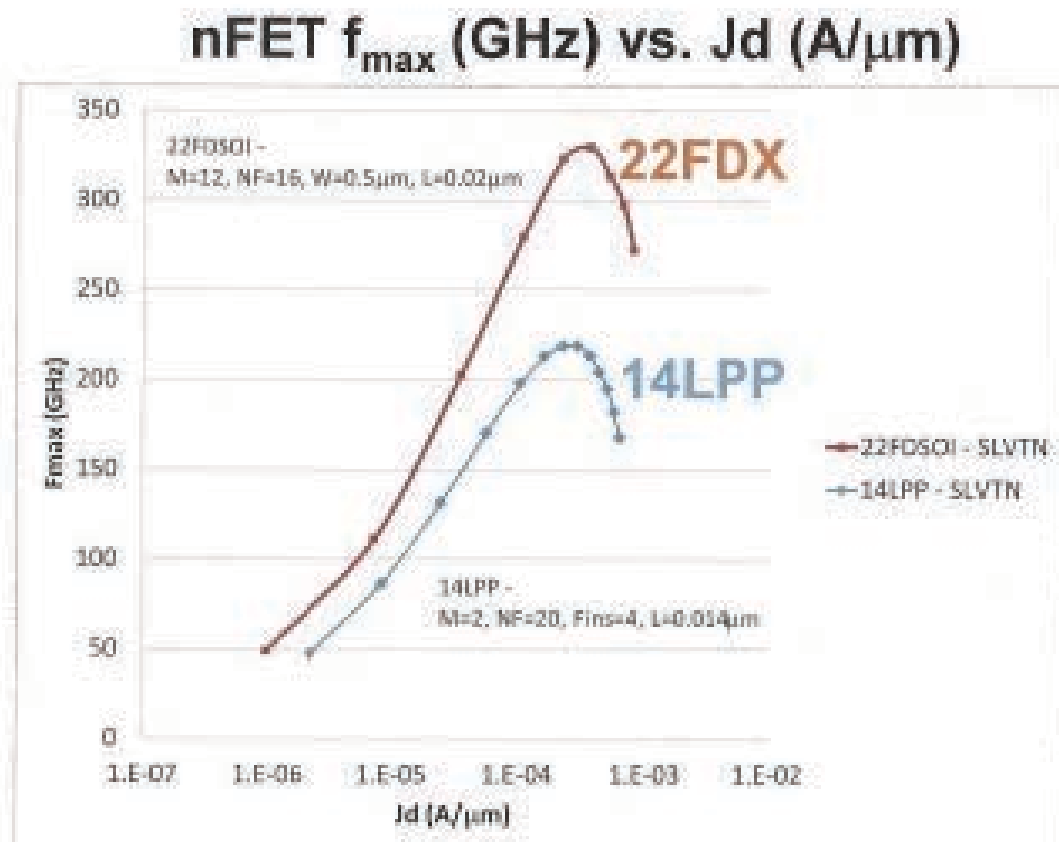
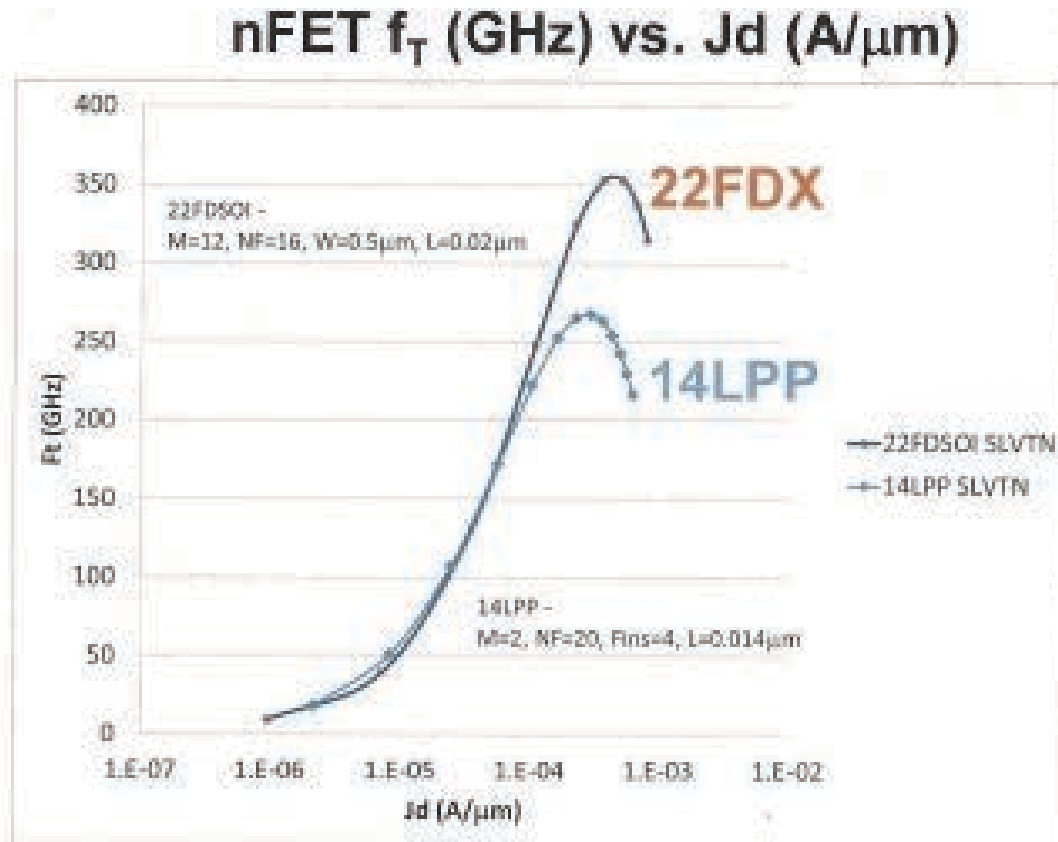
PVT List for DVFS

Domain	Process	Logic VDD (V)	Core VDD (V)	Temp ('C)
NOM (0.8v)	SSPG	0.72	0.72	-40
	SSPG	0.72	0.72	125
	SSPG	0.72	0.72	0
	FFPG	0.88	0.88	-40
	FFPG	0.88	0.88	125
	FFPG	0.88	0.88	0
	TT	0.8	0.8	0
	TT	0.8	0.8	25
	TT	0.8	0.8	85c

PVT List for Body Bias

Domain	Process	Logic VDD (V)	Core VDD (V)	Nwell body-bias (V)	Pwell body-bias (V)	Temp ('C)
NOM (0.8v)	SSPG	0.72	0.72	0.4	0.4	-40
	SSPG	0.72	0.72	0.4	0.4	125
	SSPG	0.72	0.72	0.8	0	0
	FFPG	0.88	0.88	1.4	-0.6	-40
	FFPG	0.88	0.88	1.4	-0.6	125
	FFPG	0.88	0.88	0.8	0	0
	TT	0.8	0.8	0.8	0	0
	TT	0.8	0.8	0.8	0	25
	TT	0.8	0.8	0.8	0	85c
	TT	0.8	0.8	1.1	-0.3	25
	TT	0.8	0.8	1.4	-0.6	25
	TT	0.8	0.8	0.4	0.4	25

Moving to Radio Frequency (RF)

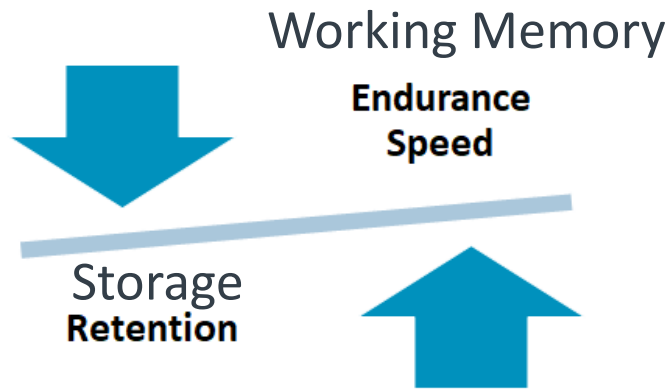


FDSOI shows better f_T and f_{max} than FinFET

eMRAM: Non-volatile Memory Solution for FDSOI

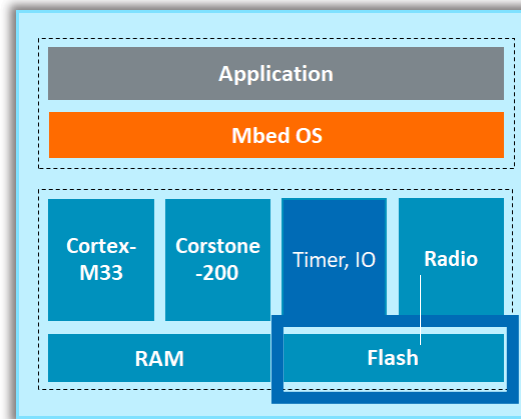
Embedded storage and working memory applications

Application-specific tuning



eMRAM for storage

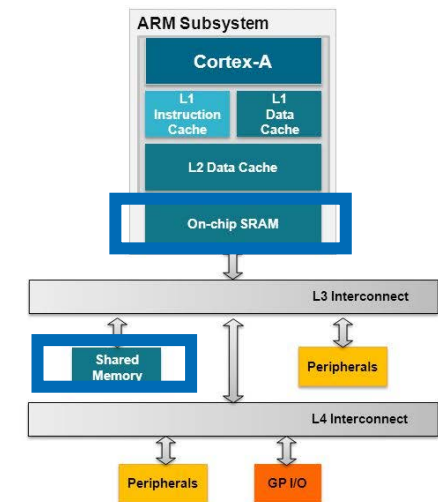
Working memory for SoC providing area, power and BoM savings



Storage memory for MCU as eFlash becomes cost-prohibitive

eMRAM as working memory

Physics results in Retention vs. Endurance/Speed trade-off



In closing

- FDSOI as a technology gives you the opportunity to reduce the bill of materials due to availability of Non-volatile memories, RF, compute horse power through biasing and knobs for power management.
 - To allow a higher adoption for FDSOI will need
 - A larger ecosystem
 - EDA tooling support
 - IP vendors who can provide guidance to navigate and use the right knobs for your design points
- FinFET is a well established process and people will continue to use this to push for compute performance and density where volume matters
 - Design complexities are being lessened due to introduction of EUV, leading to better yield
 - Cost is an inhibitor and it lacks the richness of the FDSOI process when it comes to IoT kind of applications

Silicon is the way to a connected world

arm

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Thank You

Danke

Merci

谢谢

ありがとう

Gracias

Kiitos

감사합니다

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